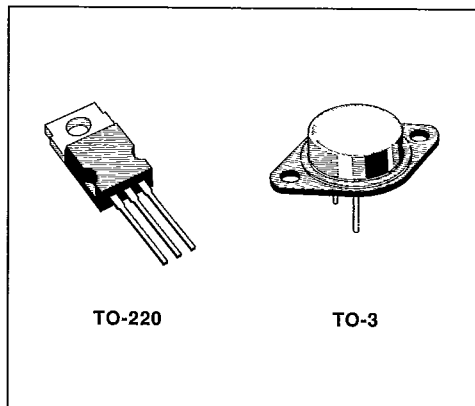


HIGH VOLTAGE POWER SWITCH

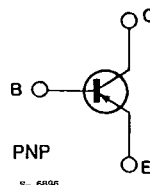
DESCRIPTION

The BUW22, BUW22A are silicon multiepitaxial mesa PNP transistor in Jedec TO-3 metal case, particularly intended for switching applications.

The BUW22P, BUW22AP are mounted in TO-220 plastic package.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BUW22/P	BUW22A/AP	
V_{CES}	Collector-emitter Voltage ($V_{BE} = 0$)	- 400	- 450	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	- 350	- 400	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	- 5	- 7	V
I_C	Collector Current	- 6		A
I_{CM}	Collector Peak Current ($t_p \leq 10$ ms)	- 8		A
I_B	Base Current	- 2		A
I_{BM}	Base Peak Current ($t_p \leq 10$ ms)	- 4		A
		TO-3	TO-220	
P_{tot}	Total Power Dissipation at $T_{case} \leq 25$ °C	75	60	W
T_{stg}	Storage Temperature	- 65 to 175	- 65 to 150	°C
T_j	Junction Temperature	175	150	°C

S G S-THOMSON

30E D

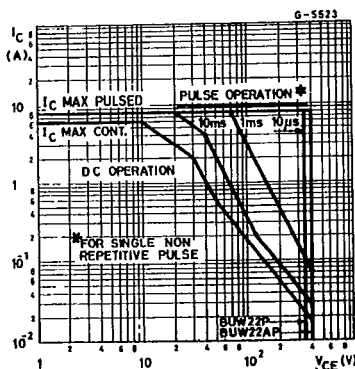
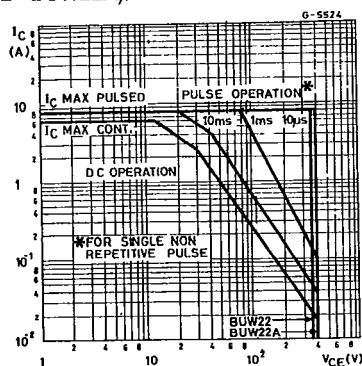
THERMAL DATA

$R_{th\ j-case}$	Thermal Resistance Junction-case	max	2	$^{\circ}C/W$
------------------	----------------------------------	-----	---	---------------

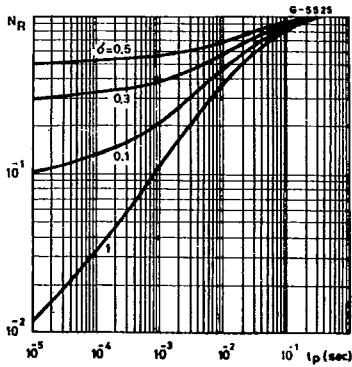
T-33-21

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

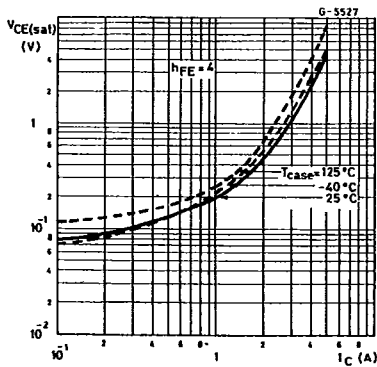
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cutoff Current ($V_{BE} = 0$)	$V_{CE} = \text{Rated } V_{CES}$ $T_{case} = 125^{\circ}C$ $V_{CE} = \text{Rated } V_{CES}$			- 1 - 5	mA mA
I_{EBO}	Collector Cutoff Current ($I_C = 0$)	$V_{EB} = \text{Rated } V_{EBO}$			- 1	mA
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = -100\text{ mA}$ for BUW22/P for BUW22A/AP	- 350 - 400			V V
$V_{CE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = -2.5\text{ A}$ $I_B = -1\text{ A}$			- 1.5	V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = -2.5\text{ A}$ $I_B = -1\text{ A}$			- 1.6	V
h_{FE}^*	DC Current Gain	$I_C = -0.5\text{ A}$ $V_{CE} = -5\text{ V}$	12			
$I_{s/b}$	Second Breakdown Collector Current	$V_{CE} = -30\text{ V}$ for BUW22/A for BUW22P/AP	- 2.5 - 2			A A
t_{on}	Turn-on Time	Resistive Load $V_{CC} = -250\text{ V}$ $I_C = -2.5\text{ A}$ $I_{B1} = -I_{B2} = -0.5\text{ A}$		0.4	0.8	μs
t_s	Storage Time			0.6	1.5	μs
t_f	Fall Time			0.3	0.7	μs

* Pulsed : pulse duration = 300 μs , duty cycle = 1.5 %.Safe Operating Areas.
(BUW22AP - BUW22P).Safe Operating Areas.
(BUW22 - BUW22A).

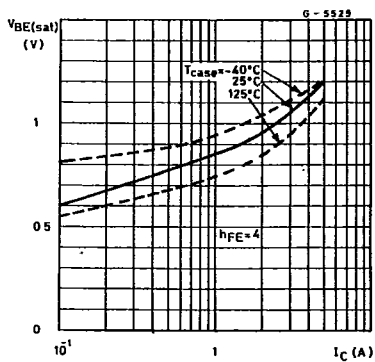
Transient Thermal Response.



Collector-emitter Saturation Voltage.

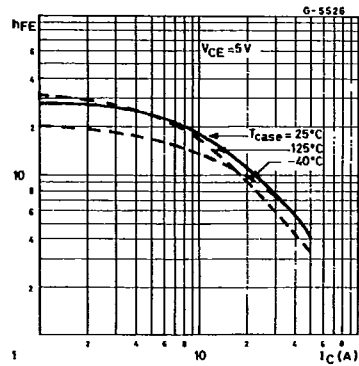


Base-emitter Saturation Voltage.

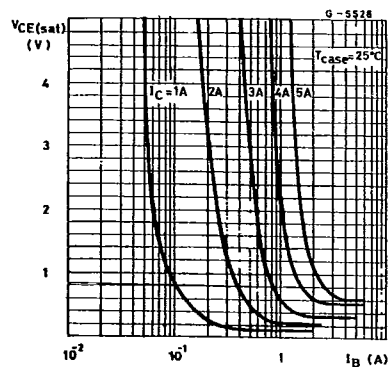


DC Current Gain.

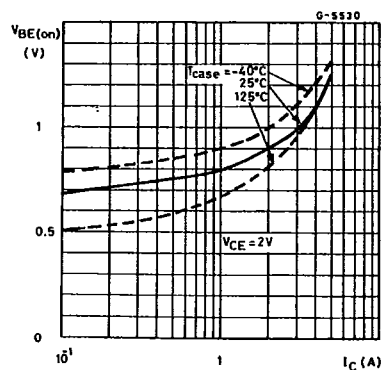
T-33-21



Collector-emitter Saturation Voltage.



Base-emitter On Voltage.

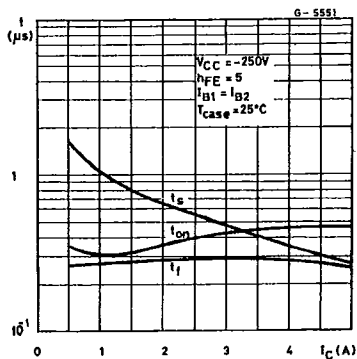


S G S-THOMSON

30E D

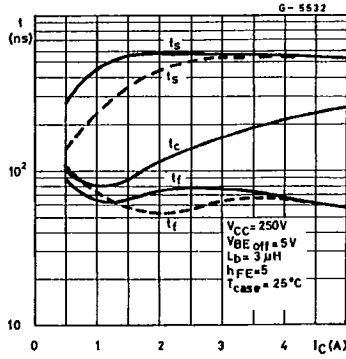
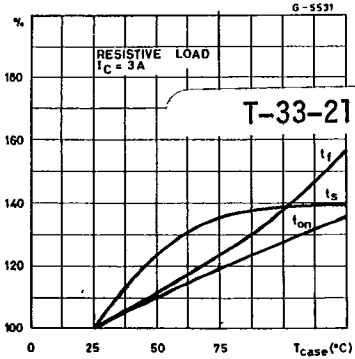
Switching Times Resistive Load (test circuit fig. 1).

Switching Time Percentage Variation vs. T_{case} .



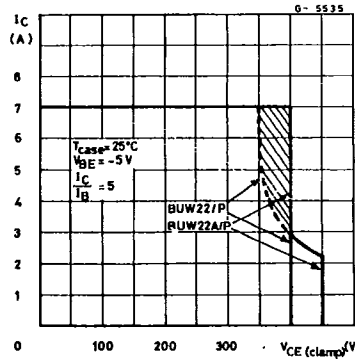
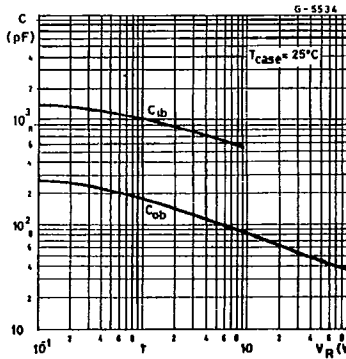
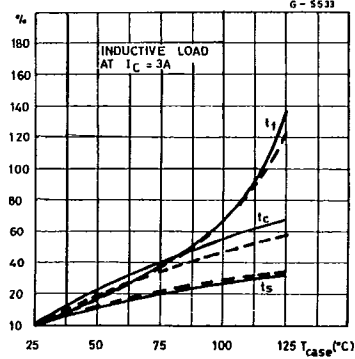
Turn-off Switching Times Inductive Load (test circuit fig. 2).

Switching Times Percentage Variation vs. T_{case} .



Capacitance.

Reserve Biased Safe Operating Area.



TEST CIRCUITS.

S G S-THOMSON

30E D

Figure 1.

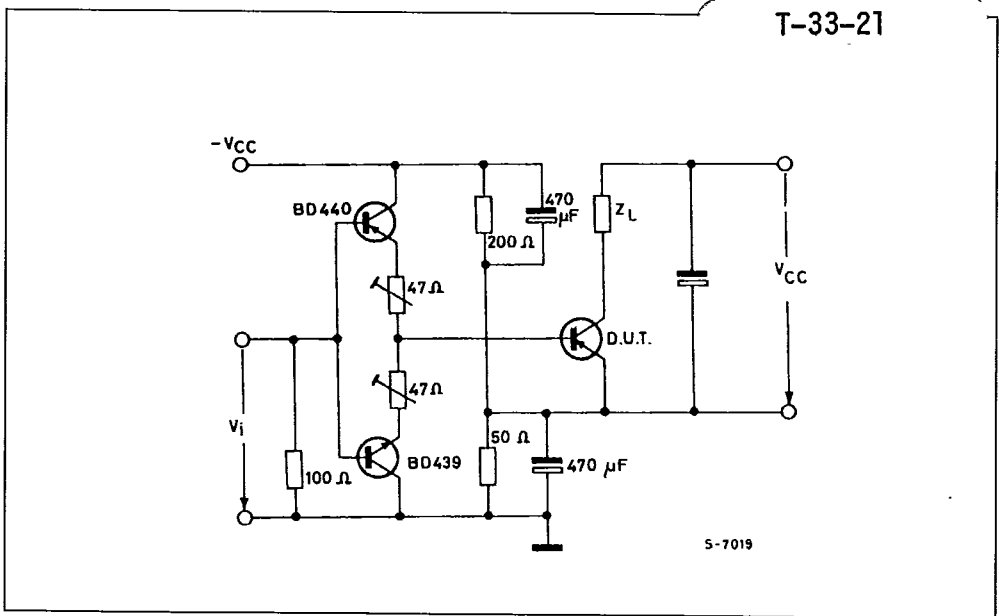


Figure 2.

